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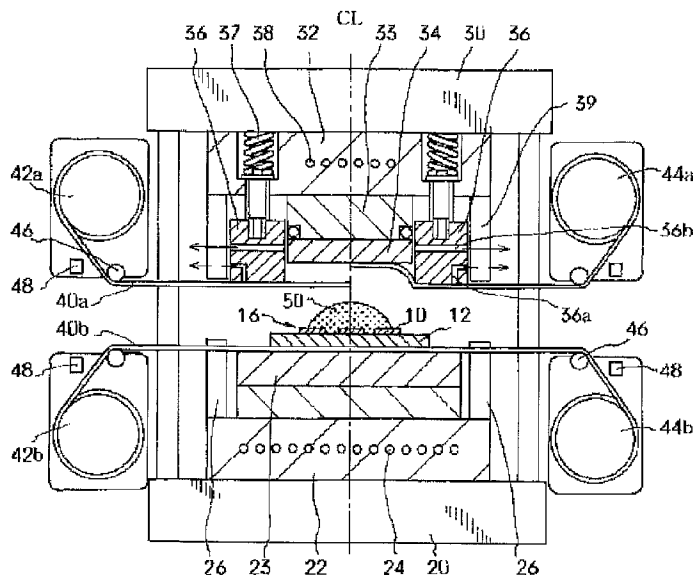
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(54) Title: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THEREOF



(57) Abstract: A method of manufacturing a semiconductor device sealed in a cured silicone body by placing an unsealed semiconductor device into a mold and subjecting a curable liquid silicone composition that fills the spaces between the mold and the unsealed semiconductor device to compression molding under a predetermined molding temperature, wherein the curable liquid silicone composition has viscosity of 90 Pa·s or less at room temperature, a time interval from the moment directly after measurement of a torque with a curometer at the molding temperature to the moment when the torque reached 1 kgf·cm being not less than 1 min., while the time



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